

General Description:

The LWS1H150A23 uses advanced SGT technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications. The package form is SOT-223, which accords with the ROHS standard and Halogen Free standard.

Features:

- Fast Switching
- Low Gate Charge and $R_{DS(ON)}$
- Low Reverse transfer capacitances

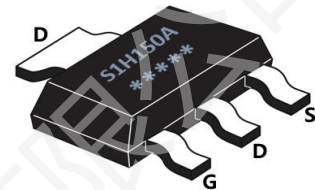
Applications:

- DC-DC Converter
- Portable Equipment
- Power Management

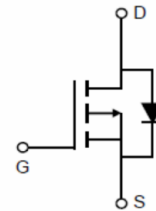


V_{DSS}	-100	V
I_D	-4.0	A
P_D	5.0	W
$R_{DS(ON)}$ TYPE	115	m Ω

Marking and Pin Assignment



Inner Equivalent Principium Chart



Package Marking and Ordering Information:

Marking	Part Number	Package	Packing	Qty.
S1H150A/D.C.	LWS1H150A23	SOT-223	Reel	1000 Pcs

Absolute Maximum Ratings:

Symbol	Parameter		Value	Units
V_{DSS}	Drain-to-Source Voltage		-100	V
I_D	Continuous Drain Current	$T_C=25^{\circ}\text{C}$	-4.0	A
	Continuous Drain Current	$T_C=100^{\circ}\text{C}$	-2.5	A
I_{DM}^{a1}	Pulsed Drain Current		-16	A
V_{GS}	Gate-to-Source Voltage		± 20	V
P_D	Power Dissipation		5.0	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range		150, -55 to 150	$^{\circ}\text{C}$
T_L	Maximum Temperature for Soldering		260	$^{\circ}\text{C}$

Thermal Characteristics:

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	25	$^{\circ}\text{C/W}$
$R_{\theta JA}^{a2}$	Thermal Resistance, Junction-to-Ambient	70	$^{\circ}\text{C/W}$

Electrical Characteristic ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise specified):

Static Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-100	--	--	V
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=-100V, V_{GS}=0V$	--	--	-1.0	μA
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=-20V, V_{DS}=0V$	--	--	-100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=+20V, V_{DS}=0V$	--	--	100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.2	-1.7	-2.2	V
$R_{DS(ON)1}$	Drain-to-Source On-Resistance	$V_{GS}=-10V, I_D=-5.0A$	--	115	150	m Ω
$R_{DS(ON)2}$	Drain-to-Source On-Resistance	$V_{GS}=-4.5V, I_D=-4.0A$	--	130	165	m Ω

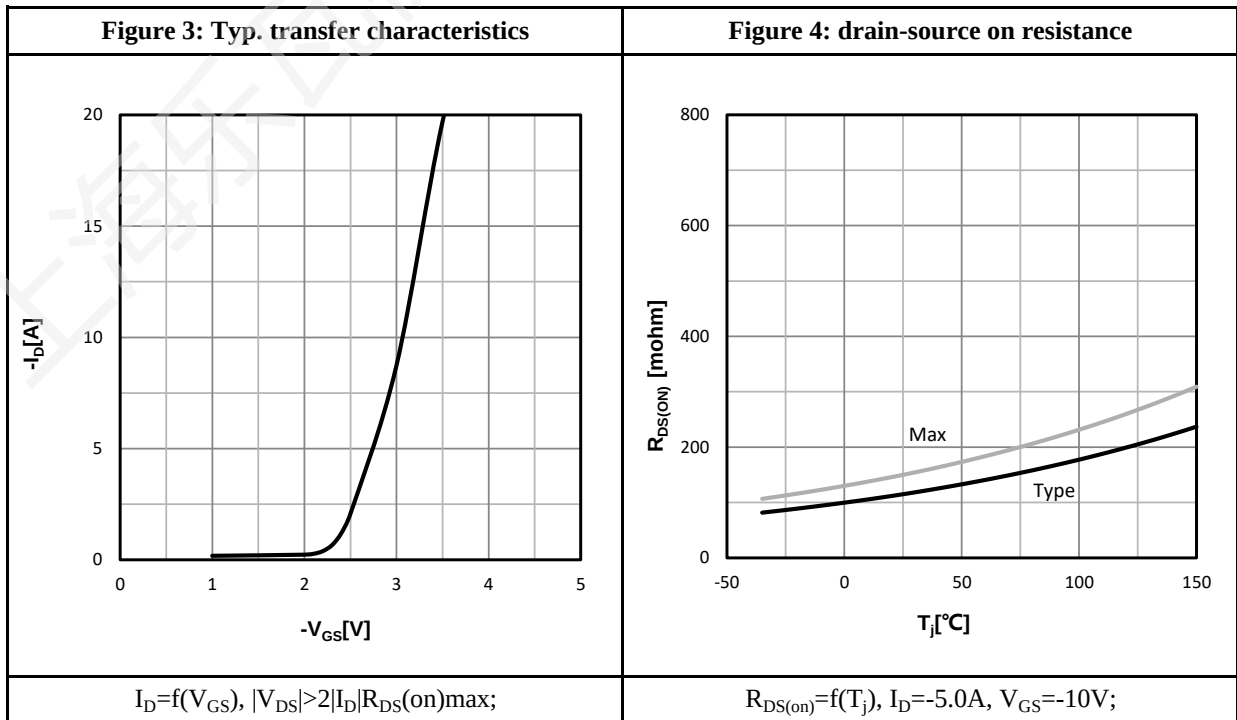
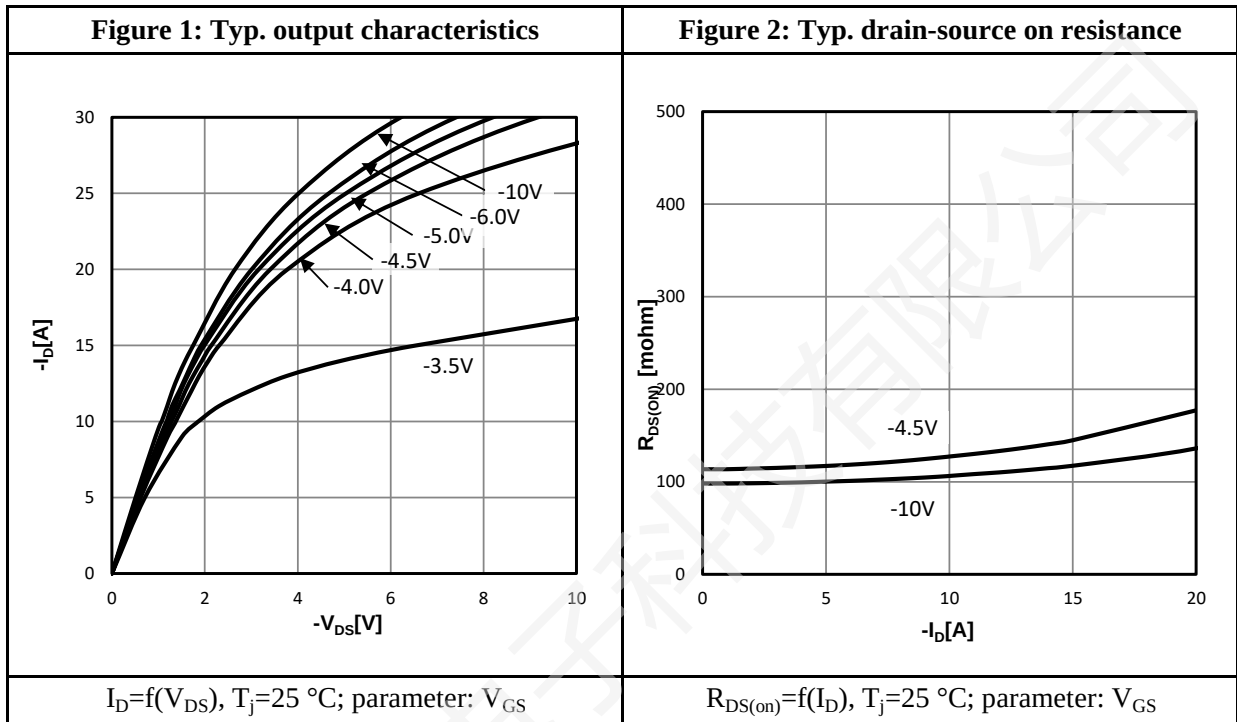
Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	$V_{GS}=0V$ $V_{DS}=-50V$ $f=1.0MHz$	--	677	--	pF
C_{oss}	Output Capacitance		--	54	--	
C_{rss}	Reverse Transfer Capacitance		--	6.6	--	
R_G	Gate resistance	$V_{GS}=0V, V_{DS}=0V, f=1MHz$	--	18	--	Ω

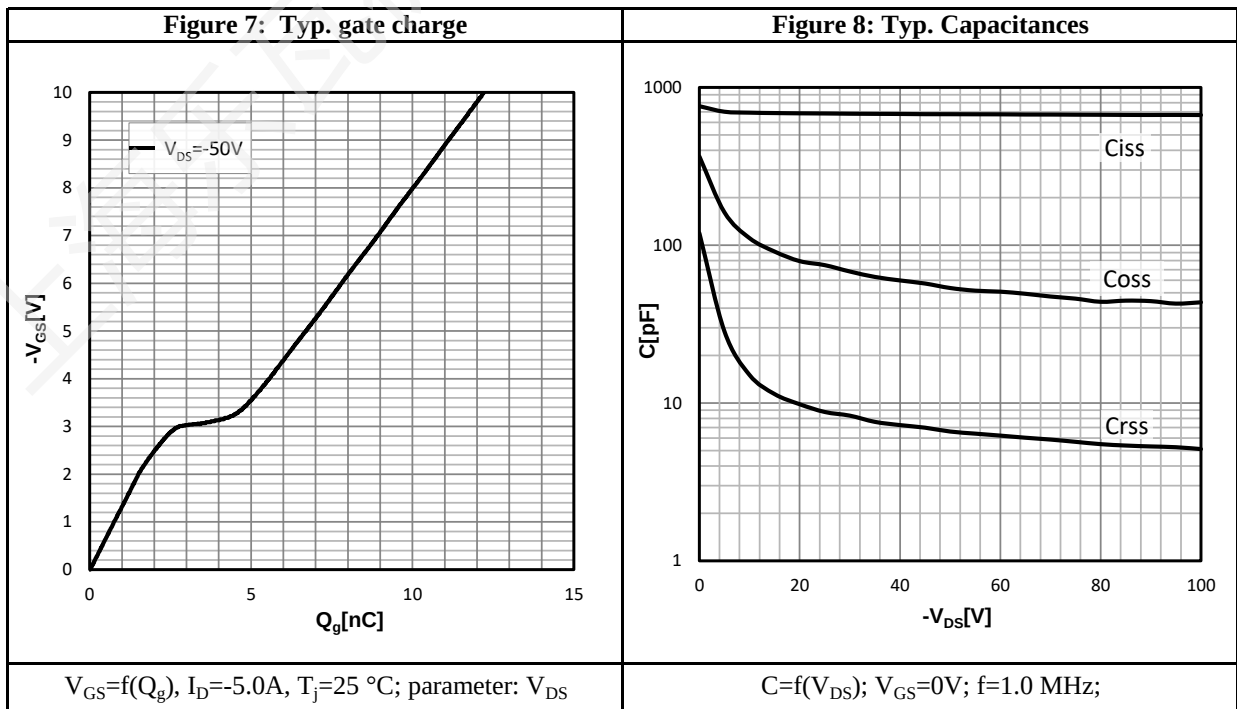
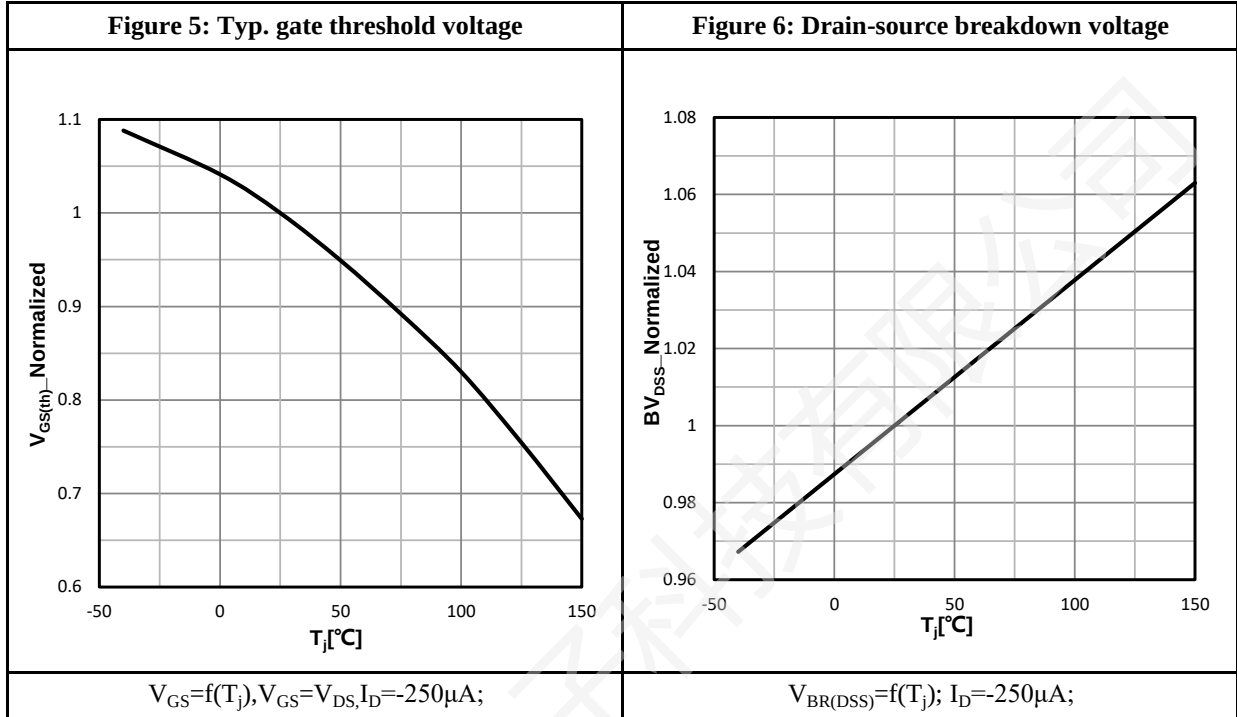
Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D=-5.0A$ $V_{DS}=-50V$ $V_{GS}=-10V$ $R_G=5.0\Omega$	--	5.9	--	ns
t_r	Rise Time		--	3.7	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	40	--	
t_f	Fall Time		--	25	--	
Q_g	Total Gate Charge	$V_{GS}=-10V$ $V_{DS}=-50V$ $I_D=-5.0A$	--	12	--	nC
Q_{gs}	Gate to Source Charge		--	2.3	--	
Q_{gd}	Gate to Drain Charge		--	1.9	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
I_S	Diode Forward Current	$T_C=25\text{ }^{\circ}\text{C}$	--	--	-4.0	A
V_{SD}	Diode Forward Voltage	$I_S=-5.0A, V_{GS}=0V$	--	--	-1.2	V
t_{rr}	Reverse Recovery Time	$I_S=-5.0A, V_{DD}=-50V$ $dI/dt=100A/\mu s$	--	66	--	ns
Q_{rr}	Reverse Recovery Charge		--	214	--	nC

a1: Repetitive rating; pulse width limited by maximum junction temperature

a2: Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection.

Characteristics Curve:




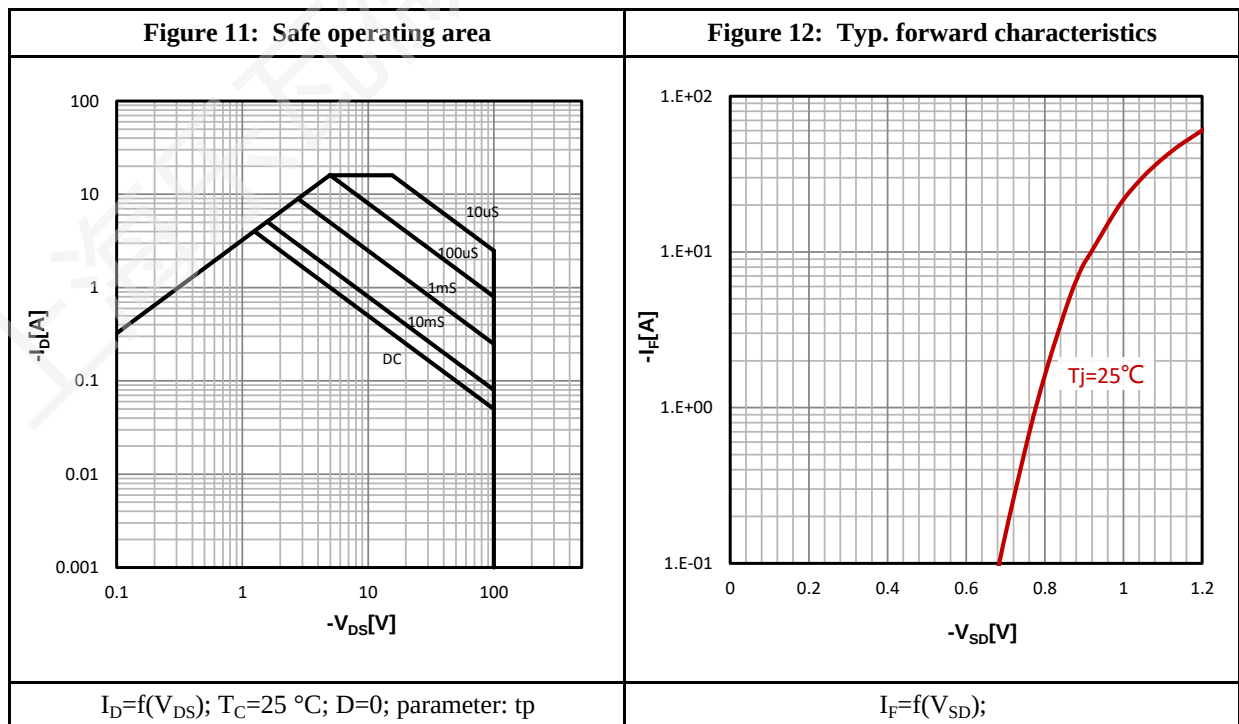
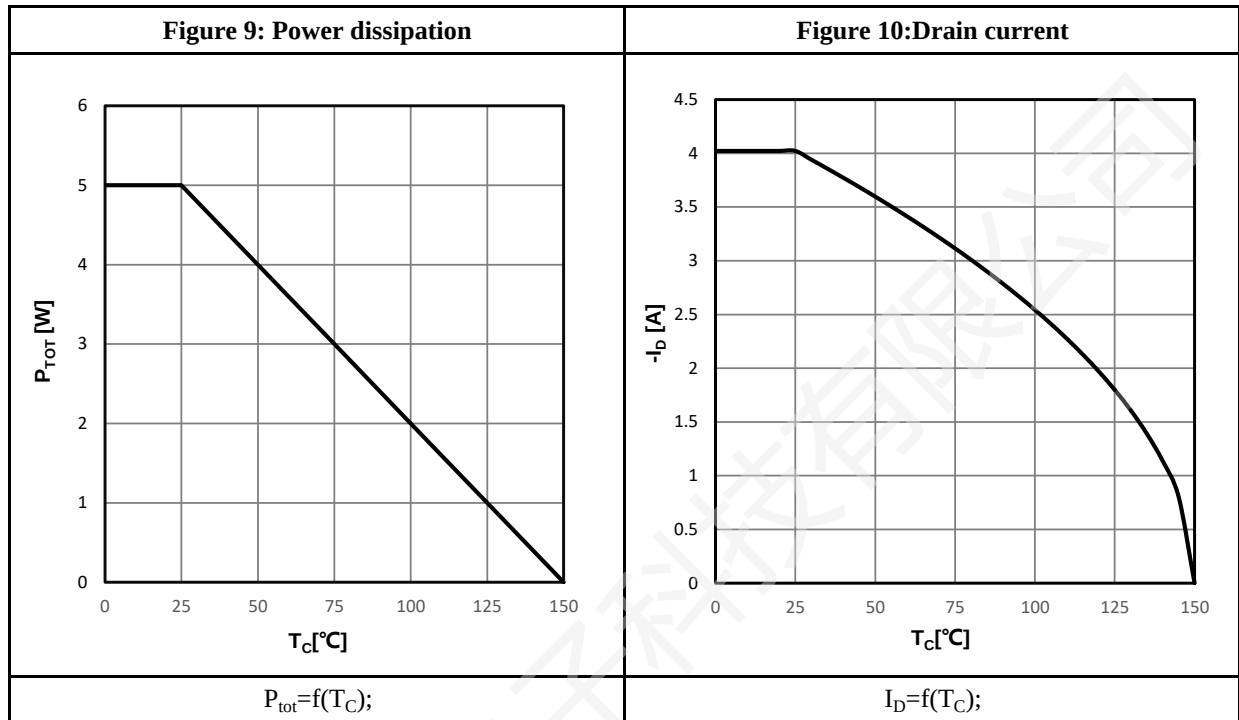
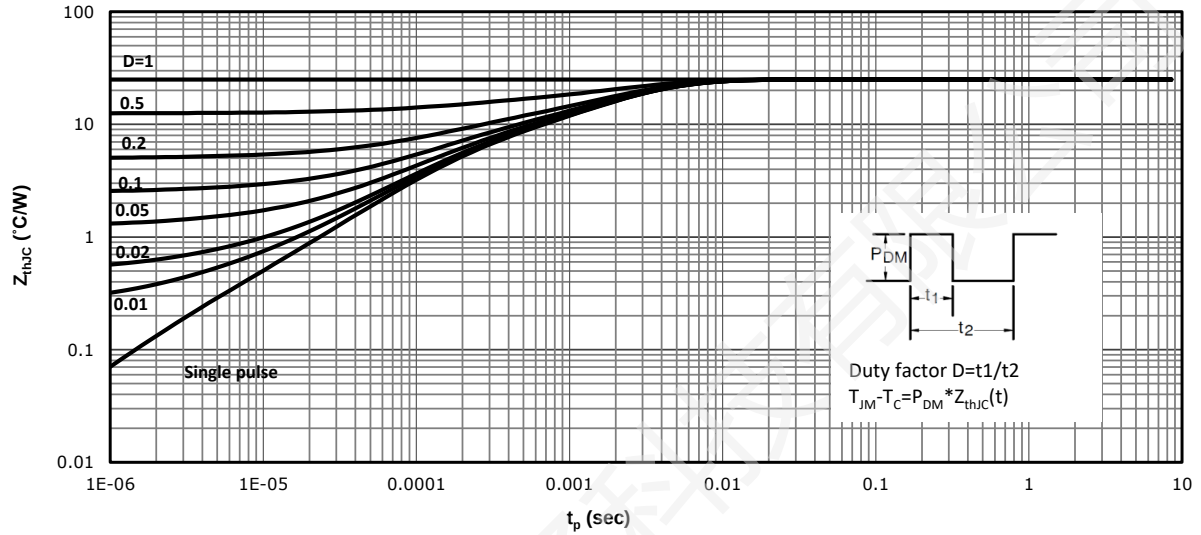
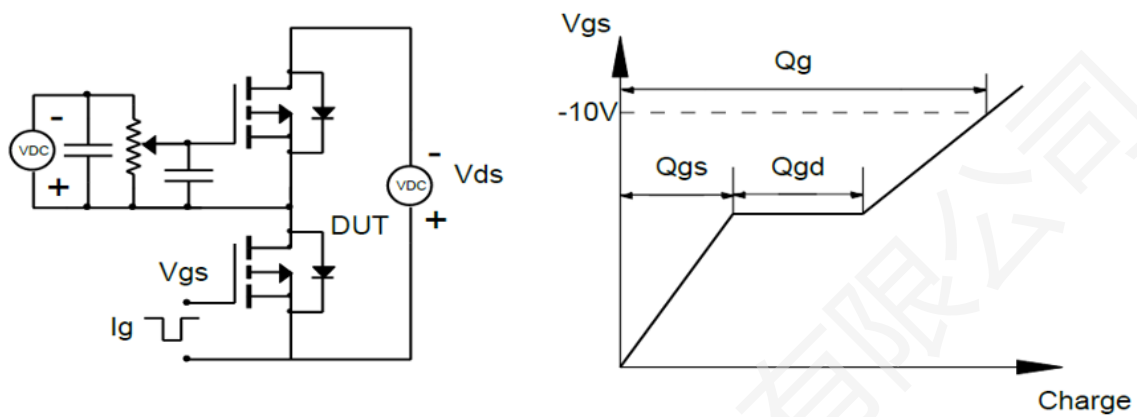
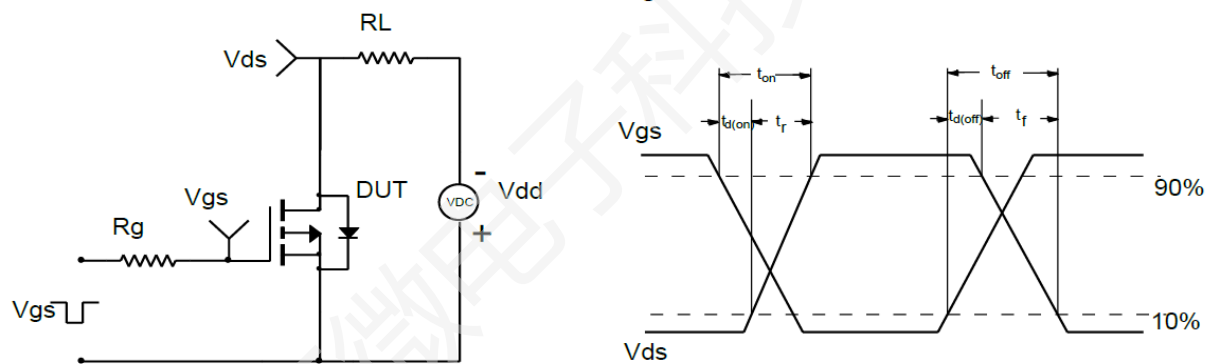
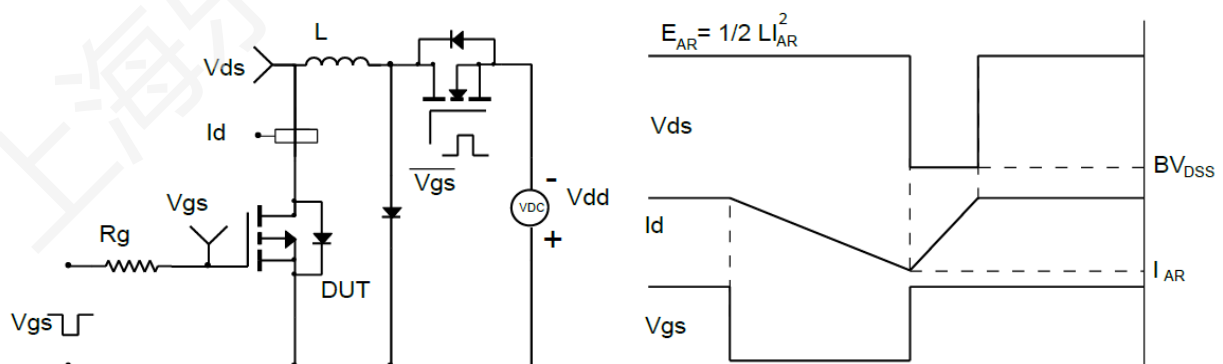
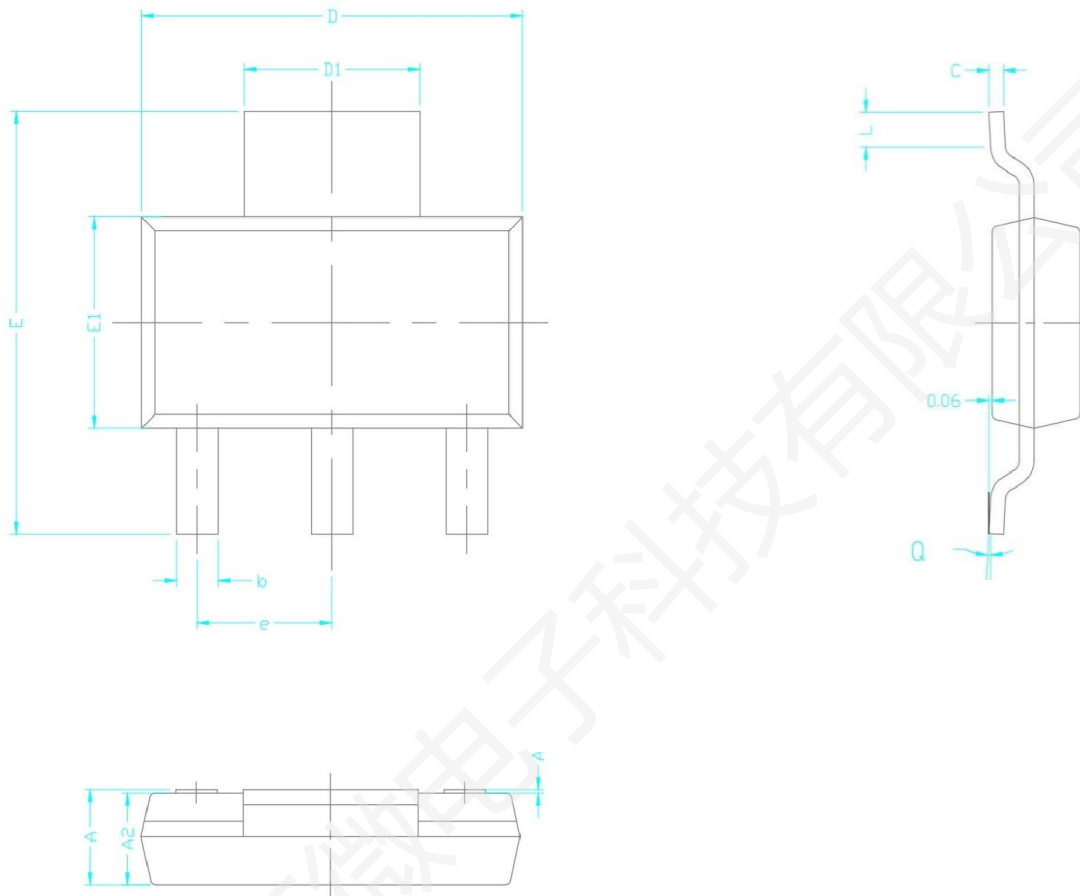


Figure 13: Max. Transient Thermal Impedance

 $Z_{thJC} = f(t_p)$; parameter: D

Test Circuit & Waveform:

Figure 14: Gate Charge Test Circuit & Waveform

Figure 15: Resistive Switching Test Circuit & Waveforms

Figure 16: Unclamped Inductive Switching Test Circuit & Waveforms

Package Outline:

COMMON DIMENSION (MM)			
PKG	TO-223		
Symbol	MIN	NOM	MAX
A	1.520	1.580	1.720
A1	0.010	0.060	0.150
A2	1.470	1.520	1.570
b	0.660	0.710	0.800
C	0.250	0.280	0.350
D	6.500	6.600	6.750
D1	2.900	3.000	3.100
E	6.700	7.000	7.300
E1	3.300	3.500	3.700
L	0.750 REF		
e	2.300 REF		
Q	0°	4°	10°

Revision History:

Revision	Date	Descriptions
Rev 1.0	Apr.2024	Initial Version

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